Contribution ID: **8** Type: **not specified**

Radiation damage investigation of epitaxial P type Silicon using Schottky diodes and pn junctions

Monday, 18 November 2019 15:40 (20 minutes)

This project investigates radiation damage of epitaxial P type silicon.

Test structures consisting of Schottky diodes and pn junctions of different size and flavors are going to be fabricated at different facilities, including RAL and Carleton.

The structures are fabricated on a 50 um thick epitaxial layer of various P type doping: 1e13, 1e14, 1e15, 1e16, and 1e17 cm-3.

Up to 25 wafers / doping level of 6 inch size will be available for device fabrication.

Update on the design, simulation and initial fabrication phase will be given. Plans for the testing of the devices will also be discussed.

Primary authors: VILLANI, Enrico Giulio (Science and Technology Facilities Council STFC (GB)); WILSON, Fergus (Science and Technology Facilities Council STFC (GB)); ZHU, Hongbo (Chinese Academy of Sciences (CN)); MANDIC, Igor (Jozef Stefan Institute (SI)); WORM, Steven (University of Birmingham)

Presenter: VILLANI, Enrico Giulio (Science and Technology Facilities Council STFC (GB))

Session Classification: Defect Characterization